Docket No. 53074-025

Declaration For Patent Application

English Language Declaration

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

BUFFER LAYER AND GROWTH METHOD FOR SUBSEQUENT EPITAXIAL GROWTH OF III-V NITRIDE SEMICONDUCTORS

the specification of which

	neck one)			
×	is attached hereto.			
	was filed on	as Unite	ed States Application No.	or PCT International
edia kak	Application Number			
74,	and was amended on _			
		(if	applicable)	
I h	ereby state that I have re luding the claims, as ame	eviewed and understand the ended by any amendment re	e contents of the above i eferred to above.	dentified specification,
kno	cknowledge the duty to common to me to be materication 1.56.	disclose to the United State al to patentability as defin	es Patent and Trademark ed in Title 37, Code of	Office all information Federal Regulations,
Se any list inv	ction 365(b) of any forei y PCT International applic ed below and have also i	ority benefits under Title 35 gn application(s) for patent cation which designated at lidentified below, by checking International application has	t or inventor's certificate least one country other tl g the box, any foreign ap	, or Section 365(a) of han the United States, oplication for patent or
Pri	or Foreign Application(s)			Priority Not Claimed
	umb out	(Occupators)	(D. (B. 11.04)	
(NU	ımber)	(Country)	(Day/Month/Year Filed)	П
(Nu	ımber)	(Country)	(Day/Month/Year Filed)	_
(Nu	ımber)	(Country)	(Day/Month/Year Filed)	

I hereby claim the benefit under application(s) listed below:	35 U.S.C. Section 119(e) of any United States provisional
(Application Serial No.)	(Filing Date)	
(Application Serial No.)	(Filing Date)	
(Application Serial No.)	(Filing Date)	
I hereby claim the benefit under 35 Section 365(c) of any PCT Internatio insofar as the subject matter of each United States or PCT International a U.S.C. Section 112, I acknowledge to Office all information known to me Section 1.56 which became available or PCT International filing date of this	nal application designating h of the claims of this app pplication in the manner p the duty to disclose to the to be material to patenta between the filing date of	the United States, listed below and, plication is not disclosed in the prior provided by the first paragraph of 35 United States Patent and Trademark ability as defined in Title 37, CFR
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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